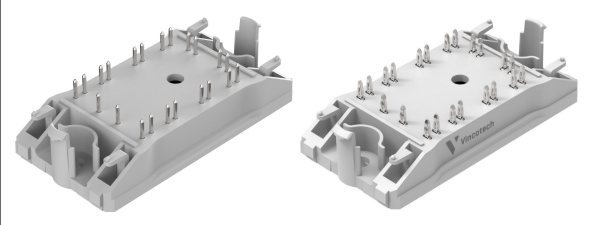
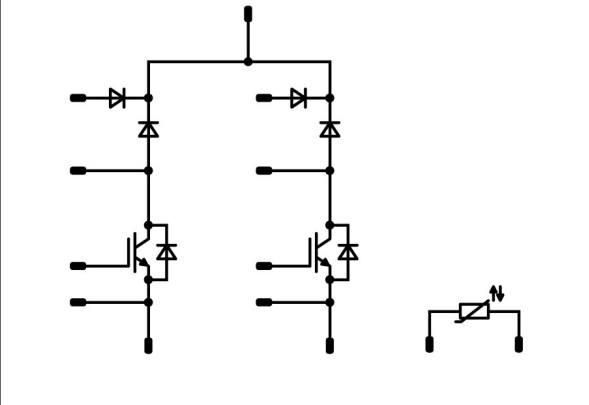




<i>flowBOOST 0</i>	1200 V / 50 A
<div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Features</p> <ul style="list-style-type: none"> High efficiency dual boost Ultra fast switching frequency Low Inductance Layout 1200V IGBT and 1200V SiC diode Antiparallel IGBT protection diode with high current </div> <div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Target applications</p> <ul style="list-style-type: none"> Solar Inverters </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Types</p> <ul style="list-style-type: none"> V23990-P629-L57-PM V23990-P629-L57Y-PM </div>	<div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> <p style="text-align: center; background-color: #ccc; margin: 0;"><i>flow 0 12mm housing</i></p>  </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Schematic</p>  </div>

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Boost Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	52	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	135	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$ $V_{CC} = 800\text{ V}$ $T_j = 150\text{ °C}$	10	µs
Maximum junction temperature	T_{jmax}		175	°C



Vincotech

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	28	A
Repetitive peak forward current	I_{FRM}		104	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave $t_p = 10\text{ ms}$ $T_j = 25\text{ °C}$	184	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	103	W
Maximum junction temperature	T_{jmax}		175	°C

Boost Sw. Protection Diode

Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	200	A
Surge current capability	I^2t		200	A ² s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	44	W
Maximum junction temperature	T_{jmax}		150	°C

ByPass Diode

Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	200	A
Surge current capability	I^2t		200	A ² s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	44	W
Maximum junction temperature	T_{jmax}		150	°C



Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
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Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{top}		-40...(T _{max} - 25)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
		AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min. 12,7	mm
Clearance		Solder pin / Press-fit pin	9,55 / 9,15	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production



Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
		V_{GS} [V]	V_{GE} [V]	V_{DS} [V]	I_D [A]	T_j [°C]	Min	Typ	Max	

Boost Switch

Static

Parameter	Symbol	$V_{GE} = V_{CE}$	V_{GS} [V]	V_{CE} [V]	I_D [A]	T_j [°C]	Min	Typ	Max	Unit
Gate-emitter threshold voltage	$V_{GE(th)}$				0,0017	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125 150	1,78	2,04 2,38 2,46	2,42	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			1	μA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							4		Ω
Input capacitance	C_{ies}	$f = 1$ Mhz	0	25		25		2770		pF
Reverse transfer capacitance	C_{res}							160		

Thermal

Parameter	Symbol	$\lambda_{paste} = 3,4$ W/mK (PSX)	V_{GS} [V]	V_{CE} [V]	I_D [A]	T_j [°C]	Min	Typ	Max	Unit
Thermal resistance junction to sink	$R_{th(j-s)}$							0,70		K/W

Dynamic

Parameter	Symbol	$R_{gon} = 8$ Ω $R_{goff} = 8$ Ω	V_{GS} [V]	V_{CE} [V]	I_D [A]	T_j [°C]	Min	Typ	Max	Unit
Turn-on delay time	$t_{d(on)}$		0 / 15	700	50	25		30		ns
Rise time	t_r					125		30		
						150		30		
						25		20		
Turn-off delay time	$t_{d(off)}$					125		21		
						150		22		
						25		335		
Fall time	t_f					125		388		
						150		408		
		25		20						
Turn-on energy (per pulse)	E_{on}	$Q_{t-FWD} = 0,3$ μC $Q_{t-FWD} = 0,5$ μC $Q_{t-FWD} = 0,5$ μC				25		2,268		mWs
						125		2,528		
						150		2,569		
Turn-off energy (per pulse)	E_{off}					25		1,970		
						125		3,327		
						150		3,752		



Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
		V_{GE} [V]	V_{CE} [V]	I_C [A]	T_j [°C]	Min	Typ	Max		

Boost Diode

Static

Forward voltage	V_F				20	25 125		1,46 1,80	1,8	V
Reverse leakage current	I_R			1200		25			600	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,92		K/W
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Dynamic

Peak recovery current	I_{RRM}					25 125 150		11 12 12		A
Reverse recovery time	t_{rr}					25 125 150		10 12 13		ns
Recovered charge	Q_r	$di/dt = 2745$ A/µs $di/dt = 2604$ A/µs $di/dt = 2496$ A/µs	0 / 15	700	50	25 125 150		0,315 0,478 0,517		µC
Reverse recovered energy	E_{rec}					25 125 150		0,105 0,210 0,230		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		3203 2883 2460		A/µs

Boost Sw. Protection Diode

Static

Forward voltage	V_F				25	25 125		1,22 1,21		V
Reverse leakage current	I_R			1600		25			50	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,59		K/W
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ByPass Diode

Static

Forward voltage	V_F				25	25 125		1,22 1,21		V
Reverse leakage current	I_R			1600		25			50	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,59		K/W
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Characteristic Values

Parameter	Symbol	Conditions				Value			Unit
		V_{GS} [V]	V_{GE} [V] V_{DS} [V]	V_{CE} [V] V_F [V]	I_D [A] I_F [A]	T_j [°C]	Min	Typ	

Thermistor

Rated resistance	R				25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 1486 \Omega$			100	-12		+14	%
Power dissipation	P				25		200		mW
Power dissipation constant					25		2		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 3\%$			25		3950		K
B-value	$B_{(25/100)}$	Tol. $\pm 3\%$			25		3998		K
Vincotech NTC Reference								B	

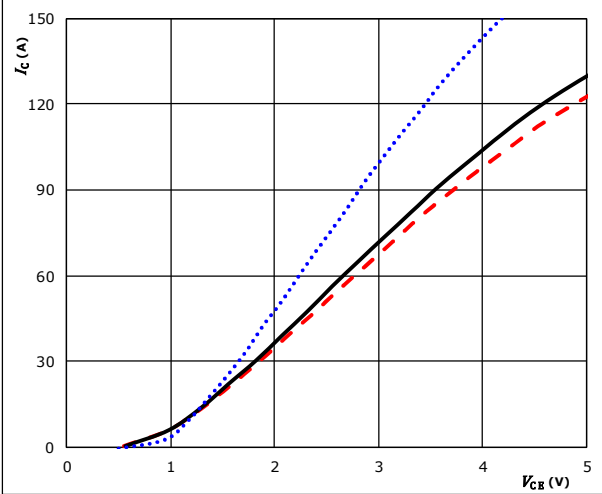


Boost Switch Characteristics

figure 1. IGBT

Typical output characteristics

$I_C = f(V_{CE})$

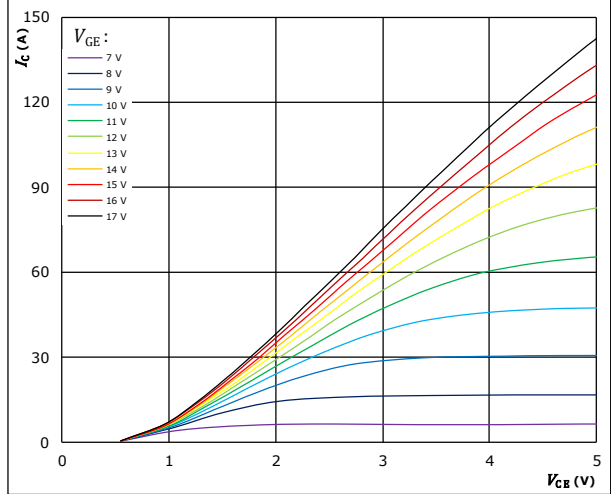


$t_p = 250 \mu s$ $T_j: 25 \text{ }^\circ C$
 $V_{GE} = 15 \text{ V}$ $T_j: 125 \text{ }^\circ C$ ———
 $T_j: 150 \text{ }^\circ C$ - - - - -

figure 2. IGBT

Typical output characteristics

$I_C = f(V_{CE})$

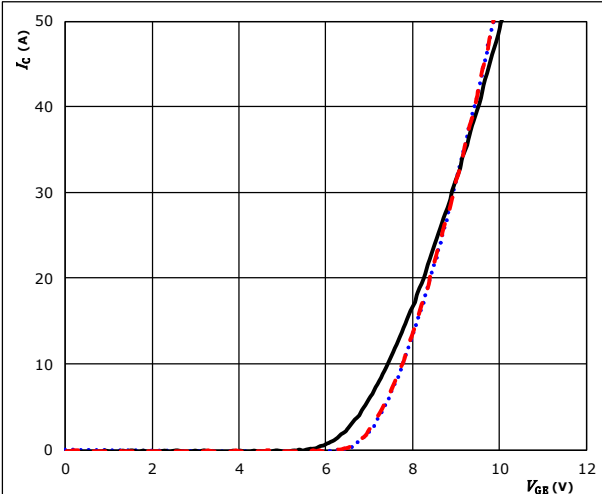


$t_p = 250 \mu s$
 $T_j = 150 \text{ }^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$

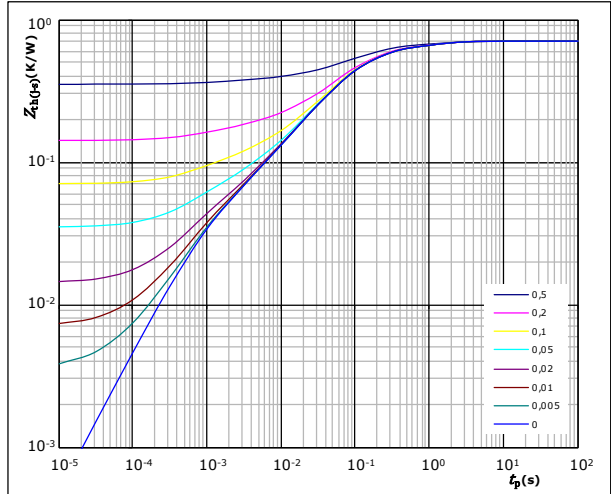


$t_p = 100 \mu s$ $T_j: 25 \text{ }^\circ C$
 $V_{CE} = 10 \text{ V}$ $T_j: 125 \text{ }^\circ C$ ———
 $T_j: 150 \text{ }^\circ C$ - - - - -

figure 4. IGBT

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$
 $R_{th(j-s)} = 0,70 \text{ K/W}$

IGBT thermal model values

R (K/W)	τ (s)
9,44E-02	1,28E+00
1,86E-01	2,02E-01
3,33E-01	6,13E-02
5,71E-02	9,05E-03
3,26E-02	9,42E-04



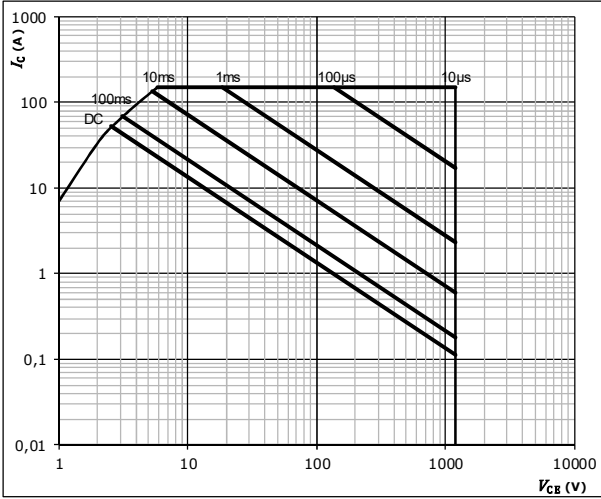
Vincotech

Boost Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



- $D =$ single pulse
- $T_s =$ 80 °C
- $V_{GE} =$ ±15 V
- $T_j =$ T_{jmax}

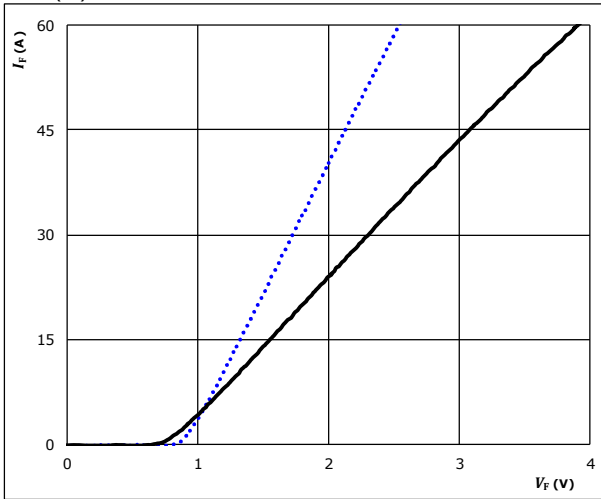


Boost Diode Characteristics

figure 1. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

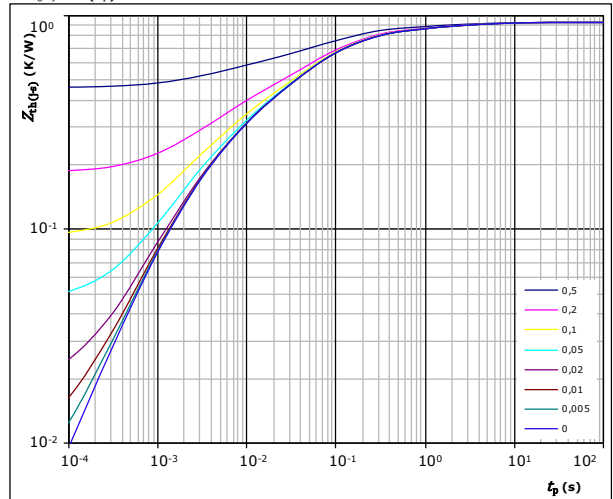


$t_p = 250 \mu s$ $T_j: 25 \text{ }^\circ\text{C}$ (dotted blue line) $125 \text{ }^\circ\text{C}$ (solid black line)

figure 2. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,92 \text{ K/W}$

FWD thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
3,98E-02	5,29E+00
8,42E-02	9,05E-01
2,67E-01	1,28E-01
2,58E-01	3,85E-02
1,93E-01	6,36E-03
7,88E-02	1,37E-03

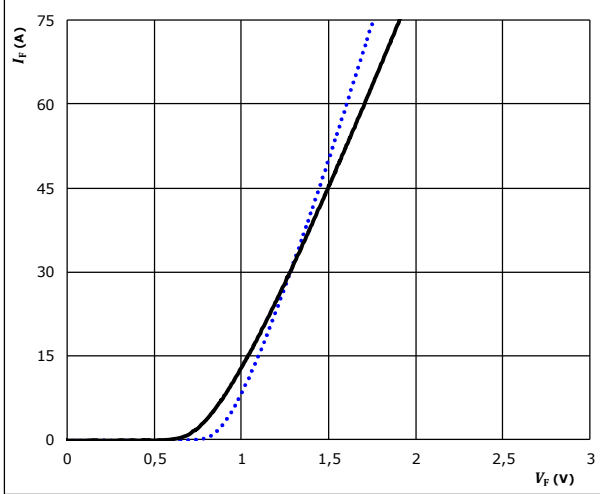


Boost Sw. Protection Diode Characteristics

figure 1. Rectifier Diode

Typical forward characteristics

$$I_F = f(V_F)$$

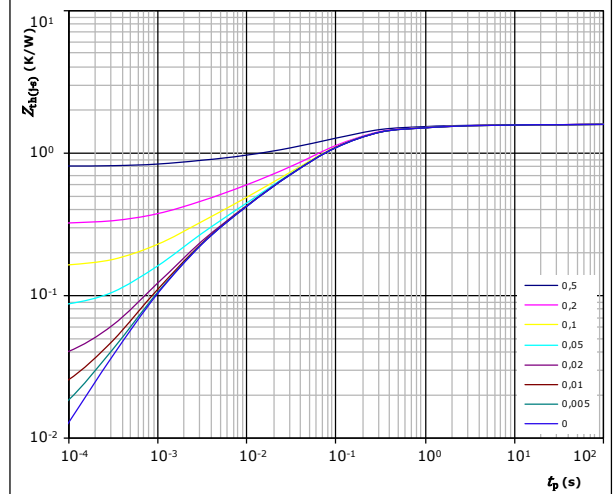


$t_p = 250 \mu s$
 $T_j: 25 \text{ }^\circ\text{C}$ (dotted blue line)
 $125 \text{ }^\circ\text{C}$ (solid black line)

figure 2. Rectifier Diode

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,59 \text{ K/W}$

Diode thermal model values

R (K/W)	τ (s)
3,44E-02	9,66E+00
1,12E-01	1,22E+00
5,81E-01	1,45E-01
4,89E-01	5,05E-02
2,38E-01	9,26E-03
1,22E-01	1,79E-03
1,81E-02	7,88E-04

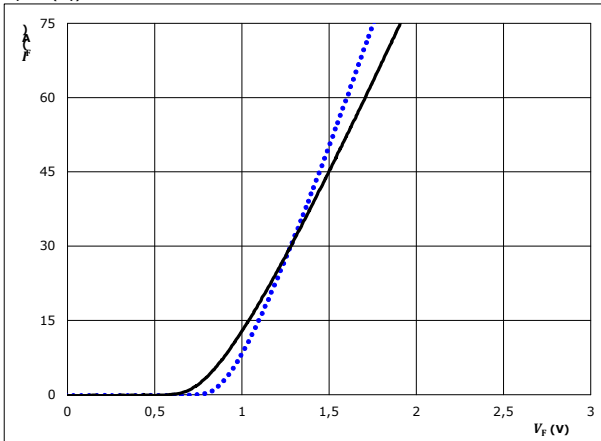


ByPass Diode Characteristics

figure 1. Rectifier Diode

Typical forward characteristics

$$I_F = f(V_F)$$

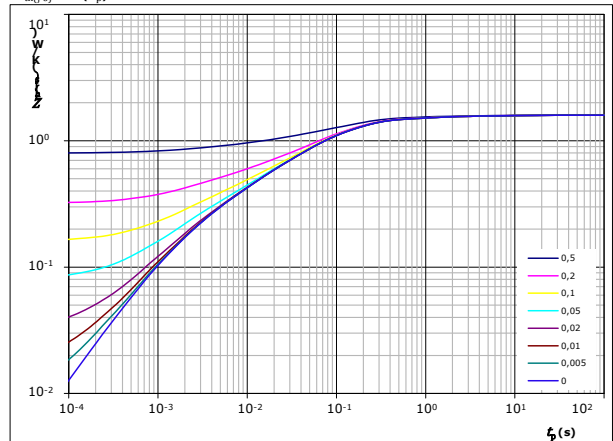


$t_p = 250 \mu s$ $T_j: 25 \text{ }^\circ\text{C}$ (dotted blue line) $125 \text{ }^\circ\text{C}$ (solid black line)

figure 2. Rectifier Diode

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,59 \text{ K/W}$

Diode thermal model values

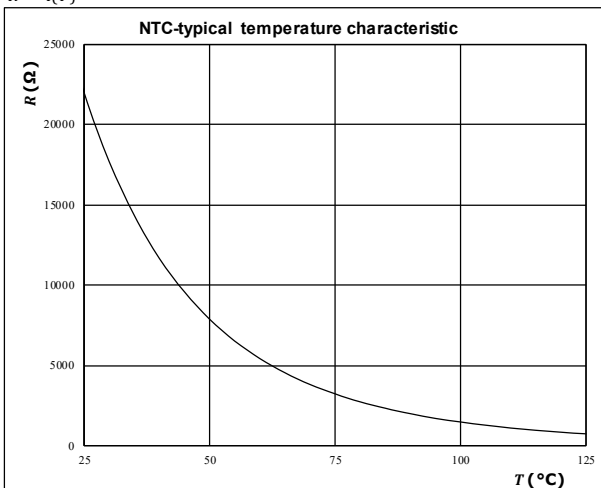
R (K/W)	τ (s)
3,44E-02	9,66E+00
1,12E-01	1,22E+00
5,81E-01	1,45E-01
4,89E-01	5,05E-02
2,38E-01	9,26E-03
1,22E-01	1,79E-03
1,81E-02	7,88E-04

Thermistor Characteristics

figure 1. Thermistor

Typical NTC characteristic
as a function of temperature

$$R = f(T)$$



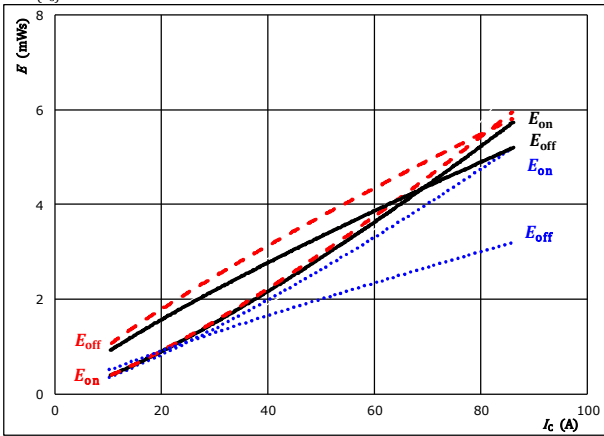


Boost Switching Characteristics

figure 1. IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_c)$$

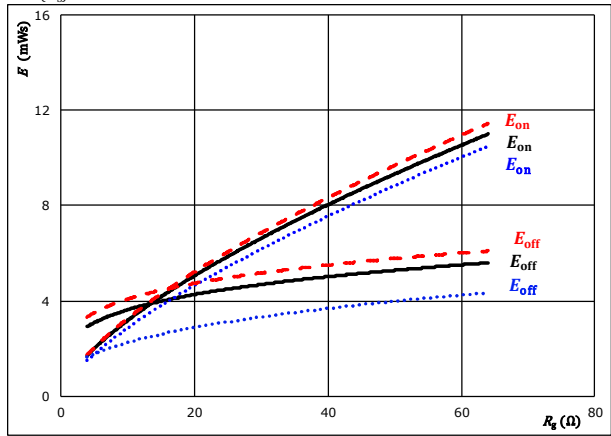


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 2. IGBT

Typical switching energy losses as a function of gate resistor

$$E = f(R_g)$$

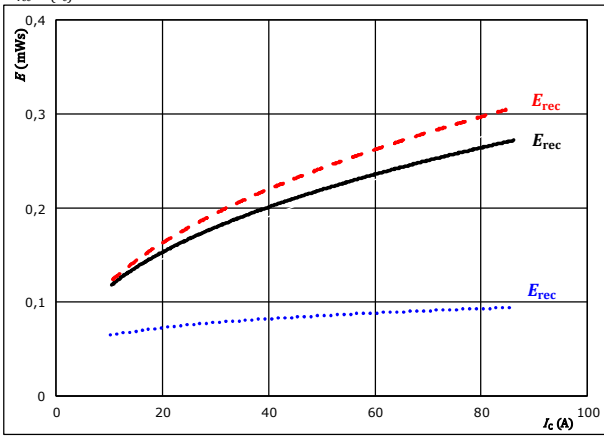


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $I_c = 50$ A
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 3. FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_c)$$

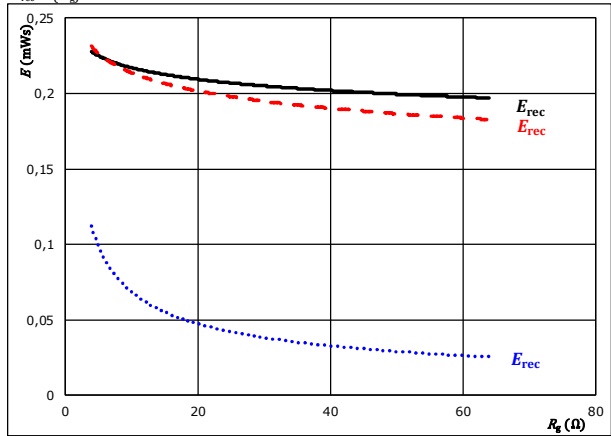


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $R_{gon} = 8$ Ω
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 4. FWD

Typical reverse recovered energy loss as a function of gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $I_c = 50$ A
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

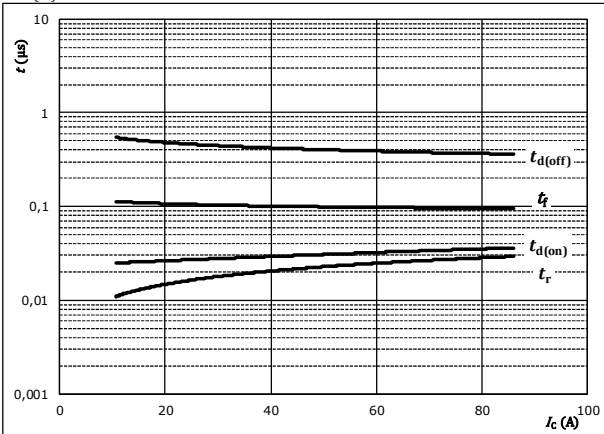


Boost Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$$t = f(I_c)$$



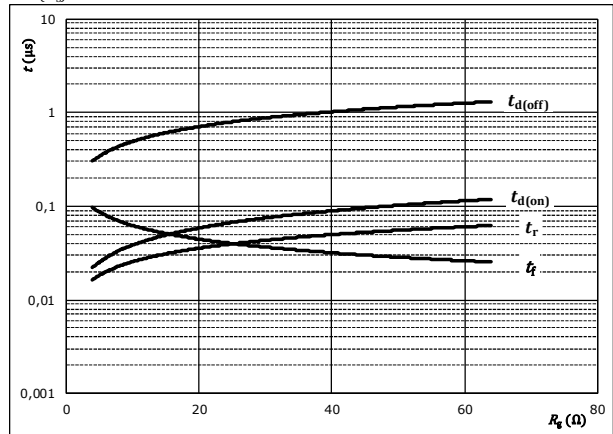
With an inductive load at

$T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $R_{g\text{on}} = 8 \text{ } \Omega$
 $R_{g\text{off}} = 8 \text{ } \Omega$

figure 6. IGBT

Typical switching times as a function of gate resistor

$$t = f(R_g)$$



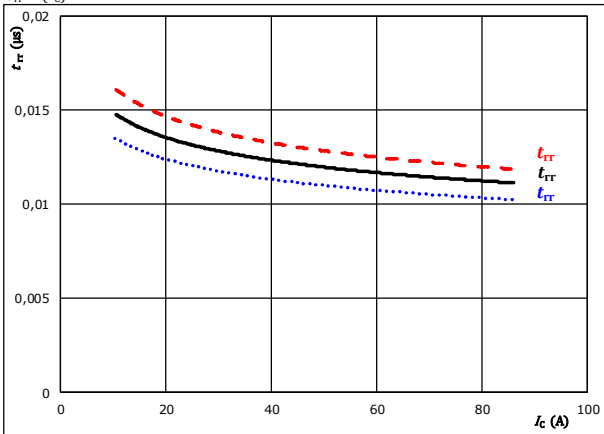
With an inductive load at

$T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $I_c = 50 \text{ A}$

figure 7. FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_c)$$



With an inductive load at

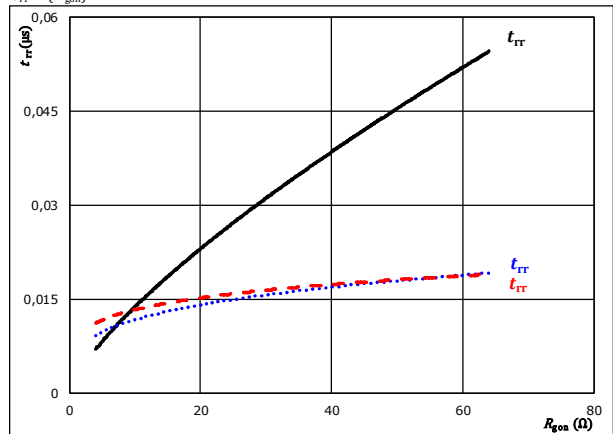
$V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $R_{g\text{on}} = 8 \text{ } \Omega$

$T_j = 25 \text{ }^\circ\text{C}$ (dotted)
 $125 \text{ }^\circ\text{C}$ (solid)
 $150 \text{ }^\circ\text{C}$ (dashed)

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{g\text{on}})$$



With an inductive load at

$V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $I_c = 50 \text{ A}$

$T_j = 25 \text{ }^\circ\text{C}$ (dotted)
 $125 \text{ }^\circ\text{C}$ (solid)
 $150 \text{ }^\circ\text{C}$ (dashed)

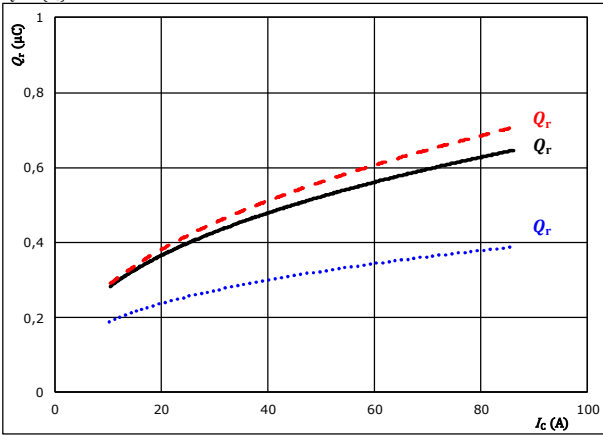


Boost Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$

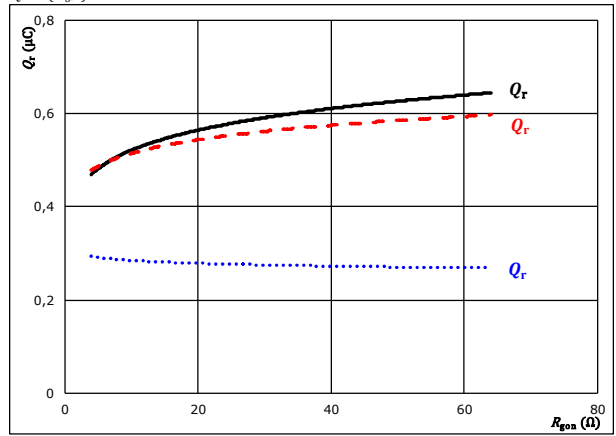


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $R_{gdn} = 8$ Ω
 T_j : 25 °C (dotted blue line)
 125 °C (solid black line)
 150 °C (dashed red line)

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gdn})$$

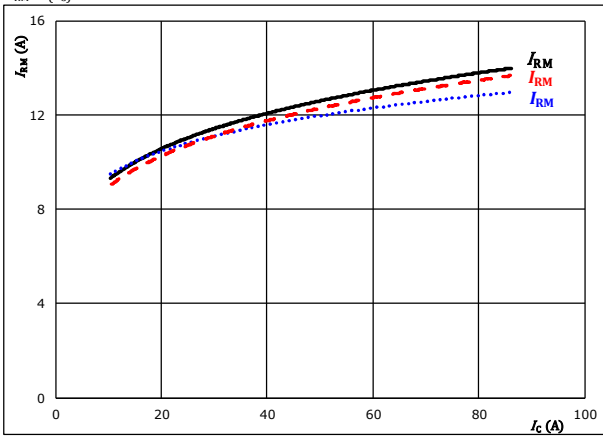


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $I_c = 50$ A
 T_j : 25 °C (dotted blue line)
 125 °C (solid black line)
 150 °C (dashed red line)

figure 11. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$

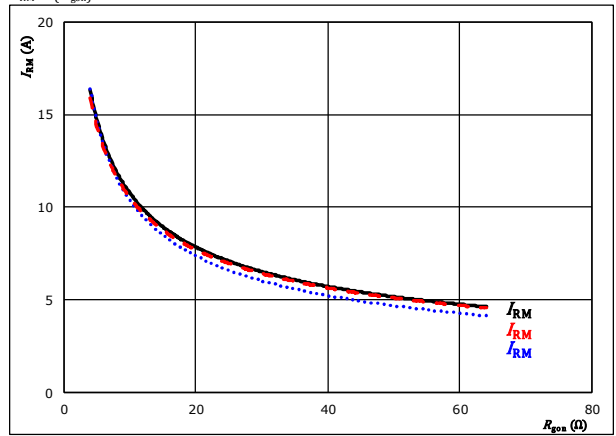


With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $R_{gdn} = 8$ Ω
 T_j : 25 °C (dotted blue line)
 125 °C (solid black line)
 150 °C (dashed red line)

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gdn})$$



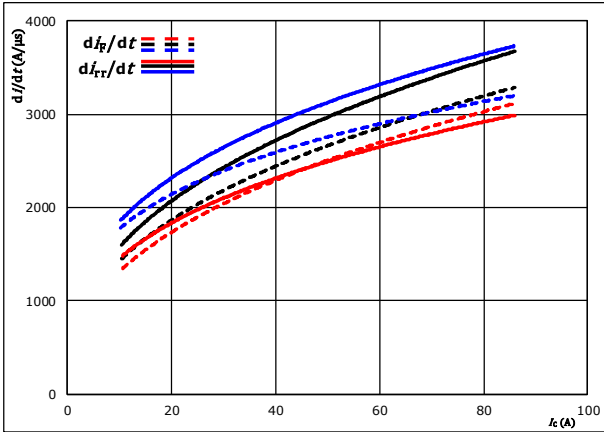
With an inductive load at
 $V_{CE} = 700$ V
 $V_{GE} = 0 / 15$ V
 $I_c = 50$ A
 T_j : 25 °C (dotted blue line)
 125 °C (solid black line)
 150 °C (dashed red line)



Boost Switching Characteristics

figure 13. FWD

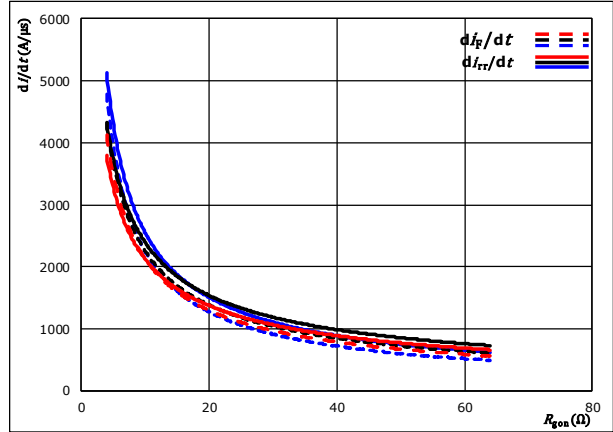
Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_F/dt, di_{rr}/dt = f(I_C)$



With an inductive load at
 $V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $R_{g\text{on}} = 8 \text{ } \Omega$
 $T_j = 25 \text{ } ^\circ\text{C}$
 $125 \text{ } ^\circ\text{C}$
 $150 \text{ } ^\circ\text{C}$

figure 14. FWD

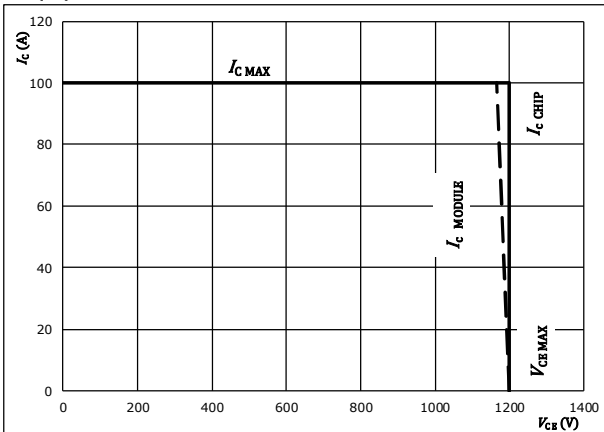
Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor
 $di_F/dt, di_{rr}/dt = f(R_{g\text{on}})$



With an inductive load at
 $V_{CE} = 700 \text{ V}$
 $V_{GE} = 0 / 15 \text{ V}$
 $I_C = 50 \text{ A}$
 $T_j = 25 \text{ } ^\circ\text{C}$
 $125 \text{ } ^\circ\text{C}$
 $150 \text{ } ^\circ\text{C}$

figure 15. IGBT

Reverse bias safe operating area
 $I_C = f(V_{CB})$



At
 $T_j = 125 \text{ } ^\circ\text{C}$
 $R_{g\text{on}} = 8 \text{ } \Omega$
 $R_{g\text{off}} = 8 \text{ } \Omega$

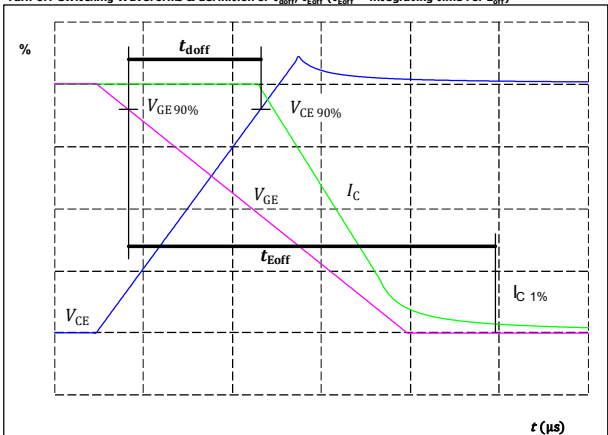


Boost Switching Definitions

General conditions		
T_j	=	125 °C
$R_{g\text{on}}$	=	8 Ω
$R_{g\text{off}}$	=	8 Ω

figure 1. IGBT

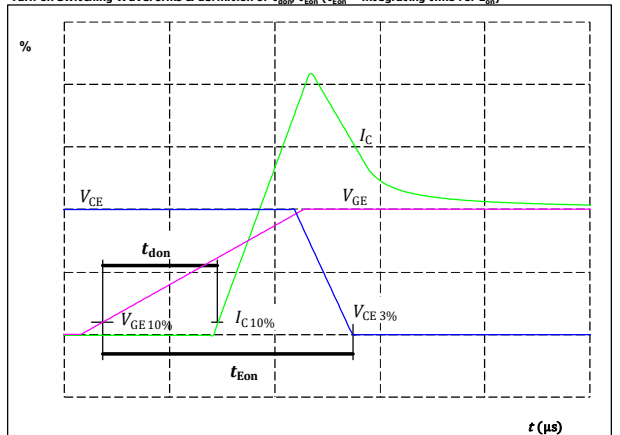
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{\text{GE}}(0\%) =$	0	V
$V_{\text{GE}}(100\%) =$	15	V
$V_{\text{C}}(100\%) =$	700	V
$I_{\text{C}}(100\%) =$	50	A
$t_{\text{doff}} =$	388	ns

figure 2. IGBT

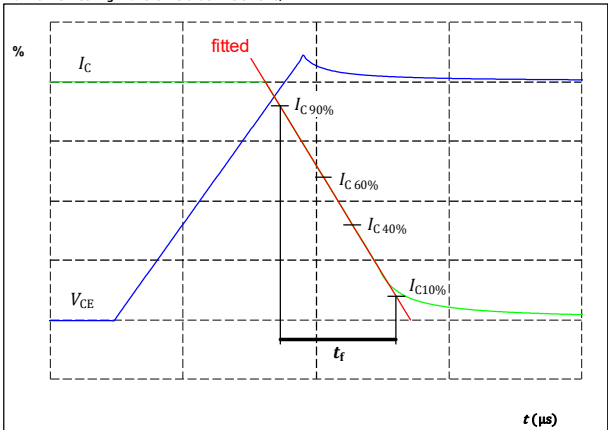
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{\text{GE}}(0\%) =$	0	V
$V_{\text{GE}}(100\%) =$	15	V
$V_{\text{C}}(100\%) =$	700	V
$I_{\text{C}}(100\%) =$	50	A
$t_{\text{don}} =$	30	ns

figure 3. IGBT

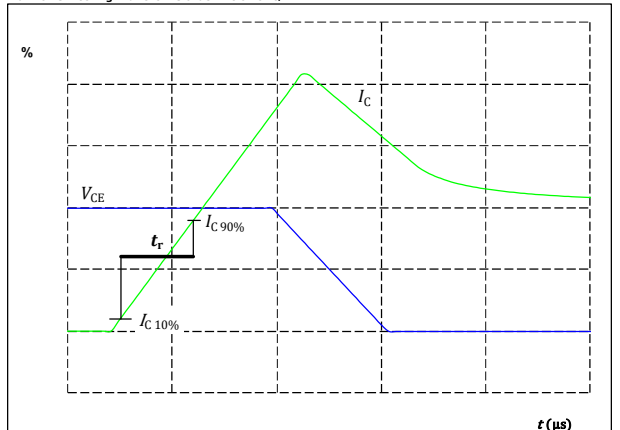
Turn-off Switching Waveforms & definition of t_r



$V_{\text{C}}(100\%) =$	700	V
$I_{\text{C}}(100\%) =$	50	A
$t_r =$	56	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r



$V_{\text{C}}(100\%) =$	700	V
$I_{\text{C}}(100\%) =$	50	A
$t_r =$	21	ns

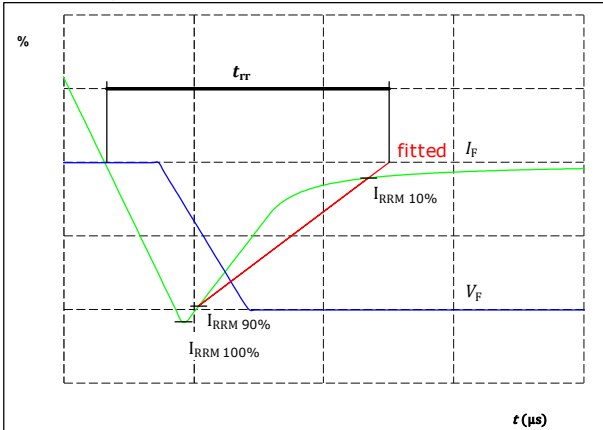


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Boost Switching Characteristics

figure 5. FWD

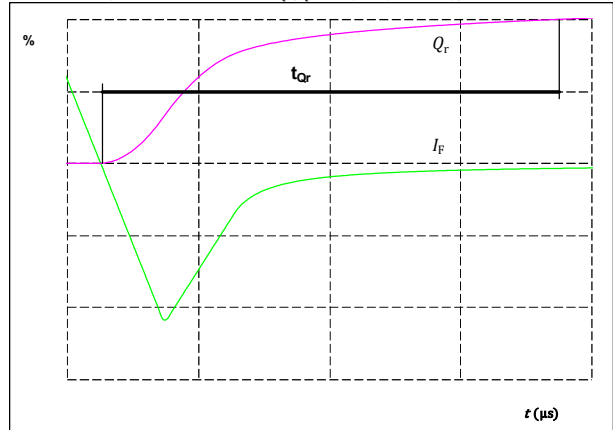
Turn-off Switching Waveforms & definition of t_{rr}



$V_F(100\%) =$	700	V
$I_F(100\%) =$	50	A
$I_{RRM}(100\%) =$	12	A
$t_{rr} =$	12	ns

figure 6. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



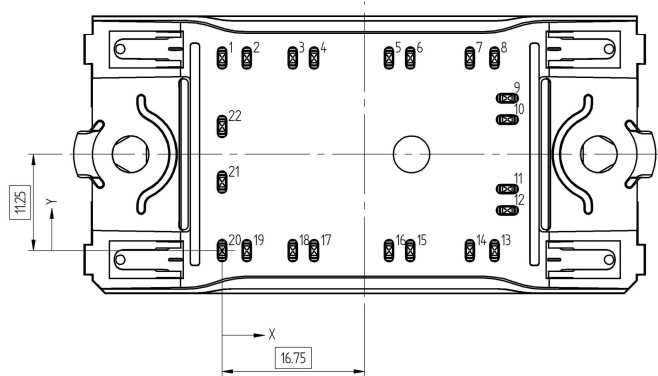
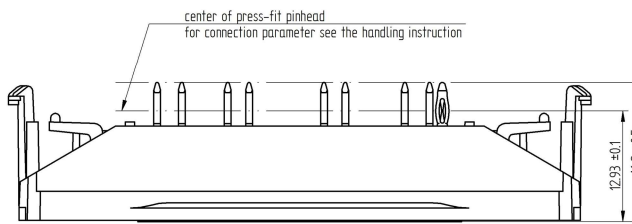
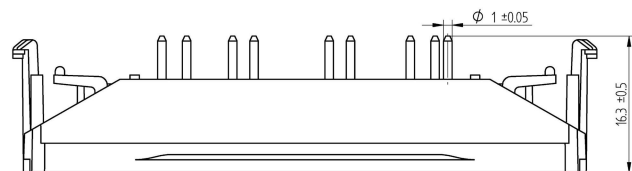
$I_F(100\%) =$	50	A
$Q_r(100\%) =$	0,48	μC



Ordering Code & Marking							
Version				Ordering Code			
12 mm housing with solder pin without thermal paste				V23990-P629-L57-PM			
12 mm housing with pressfit pin without thermal paste				V23990-P629-L57Y-PM			
Text	VIN	Date code	Name&Ver	UL	Lot	Serial	
	VIN	WWYY	NNNNNNNVV	UL	LLLLL	SSSS	
Datamatrix	Type&Ver	Lot number	Serial	Date code			
	TTTTTTTVV	LLLLL	SSSS	WWYY			

Outline

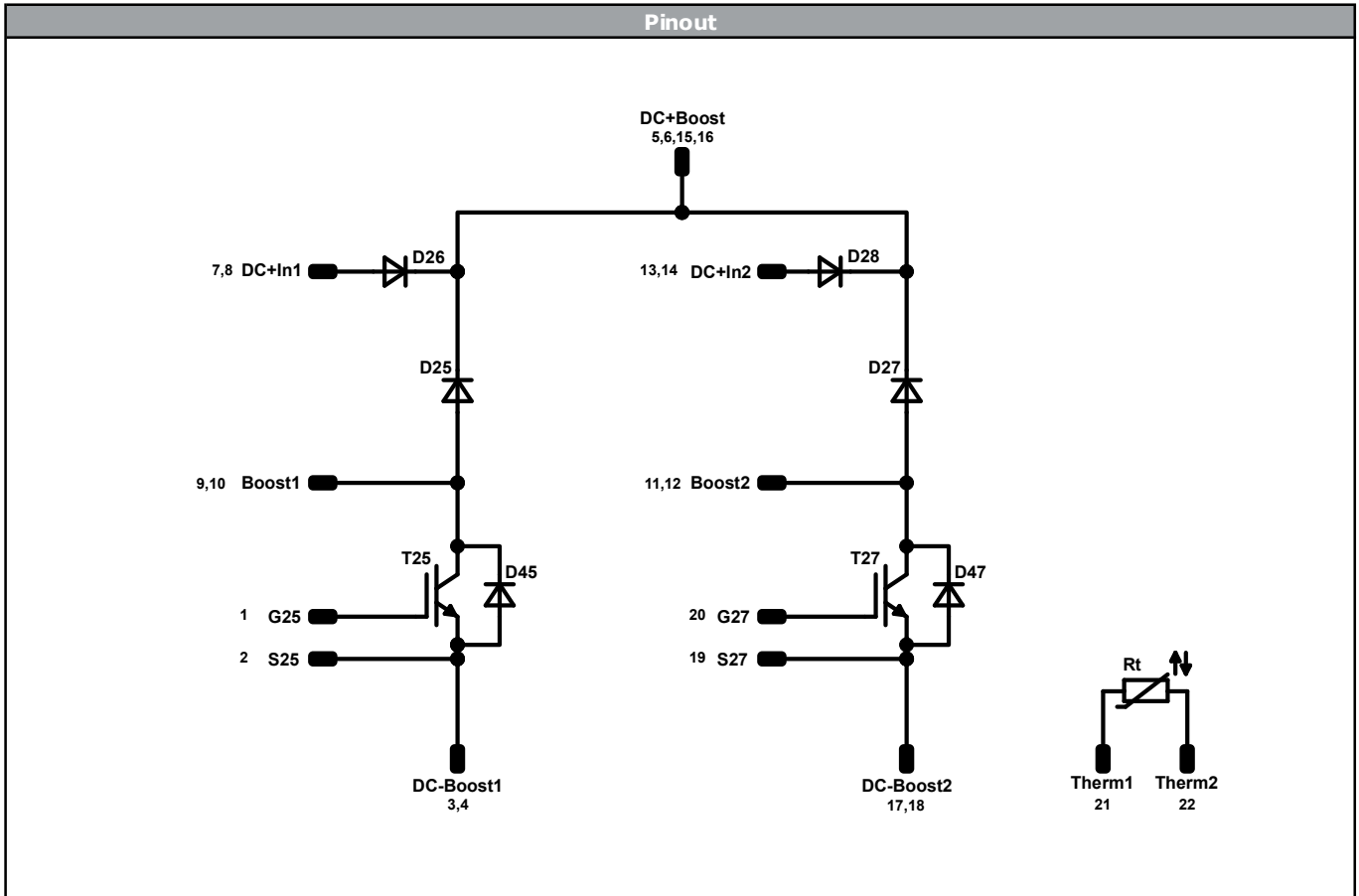
Pin table			
Pin	X	Y	Function
1	0	22,5	G25
2	2,9	22,5	S25
3	8,3	22,5	DC-Boost1
4	10,8	22,5	DC-Boost1
5	19,6	22,5	DC+Boost
6	22,1	22,5	DC+Boost
7	29,1	22,5	DC+In1
8	32	22,5	DC+In1
9	33,5	17,8	Boost1
10	33,5	15,3	Boost1
11	33,5	7,2	Boost2
12	33,5	4,7	Boost2
13	32	0	DC+In2
14	29,1	0	DC+In2
15	22,1	0	DC+Boost
16	19,6	0	DC+Boost
17	10,8	0	DC-Boost2
18	8,3	0	DC-Boost2
19	2,9	0	S27
20	0	0	G27
21	0	8	Therm1
22	0	14,5	Therm2



Tolerance of pinpositions: ± 0.5 mm at the end of pins
 Dimension of coordinate axis is only offset without tolerance



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Identification					
ID	Component	Voltage	Current	Function	Comment
T25, T27	IGBT	1200 V	50 A	Boost Switch	
D25, D27, D25, D27	FWD	1200 V	20 A	Boost Diode	
D45, D47	FWD	1600 V	25 A	Boost Sw. Protection Diode	
D26, D28	FWD	1600 V	25 A	ByPass Diode	
Rt	NTC			Thermistor	




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Packaging instruction			
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ Sample

Handling instruction
Handling instructions for <i>flow 0</i> packages see vincotech.com website.

Package data
Package data for <i>flow 0</i> packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

Document No.:	Date:	Modification:	Pages
V23990-P629-L57x-D2-14	10 Apr. 2019	Correction of I_c/I_f values	1,2

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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